Abstract Submitted for the MAR12 Meeting of The American Physical Society

Influence of growth parameters on the spin-filtering properties of epitaxial ferrite tunnel barriers<sup>1</sup> J.-B. MOUSSY<sup>2</sup>, S. MATZEN<sup>3</sup>, CEA-Saclay, R. MATTANA<sup>4</sup>, F. PETROFF<sup>5</sup>, UMR CNRS/Thales, G.-X. MIAO<sup>6</sup>, J.S. MOODERA<sup>7</sup>, Francis Bitter Magnet Lab., CEA TEAM, UMR CNRS/THALES TEAM, MIT TEAM In spintronics, spin-filtering is a physical phenomenon which has the potential to produce highly spin-polarized currents by the spin-selective transport of electrons across a ferromagnetic tunnel barrier. The insulating ferrites MnFe<sub>2</sub>O<sub>4</sub>, CoFe<sub>2</sub>O<sub>4</sub> and NiFe<sub>2</sub>O<sub>4</sub>, whose Curie temperatures are above 300K, are promising candidates for spin-filtering at room temperature. In this work, we report on the in-depth study of structural, chemical and physical properties of epitaxial ferrite ultra-thin films and associated spin-filtering measurements as a function of different growth parameters. We analyze the effect of oxidation on the physical properties and the resultant spin-polarization. The influence of structural defects on the spin-filter efficiency is also put on view by tunneling magnetoresistance. Finally, we show the impact of the  $MgAl_2O_4(001)$  substrates on the magnetic behavior of cobalt ferrite tunnel barriers revealing the important role played by strains in the spin-filter properties.

<sup>1</sup>This work is supported by the Partner University Fund <sup>2</sup>IRAMIS, SPCSI, 91191 Gif-sur-Yvette, France <sup>3</sup>IRAMIS, SPCSI, 91191 Gif-sur-Yvette, France <sup>4</sup>UMR CNRS/Thales, 91767 Palaiseau, France <sup>5</sup>UMR CNRS/Thales, 91767 Palaiseau, France <sup>6</sup>Phys. Dep., Massachusetts Institute of Technology, Cambridge, MA <sup>7</sup>Phys. Dep., Massachusetts Institute of Technology, Cambridge, MA

Date submitted: 10 Nov 2011

Electronic form version 1.4